

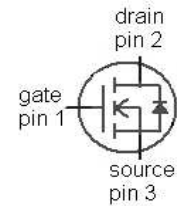
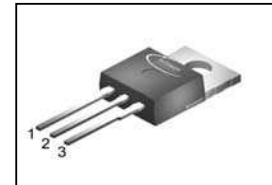
**CoolMOS™ Power Transistor**
**Features**

- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- High peak current capability
- Ultra low effective capacitances
- Extreme  $dv/dt$  rated
- Improved transconductance

**Product Summary**

$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	0.75	$\Omega$
$I_D$	6.2	A

PG-TO220-3-1



Type	Package	Ordering Code	Marking
SPP06N60C3	PG-TO220-3-1	Q67040-S4629	06N60C3

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$T_C=25\text{ °C}$	6.2	A
		$T_C=100\text{ °C}$	3.9	
Pulsed drain current <sup>1)</sup>	$I_{D,pulse}$	$T_C=25\text{ °C}$	18.6	
Avalanche energy, single pulse	$E_{AS}$	$I_D=3.1\text{ A}, V_{DD}=50\text{ V}$	200	mJ
Avalanche energy, repetitive $t_{AR}$ <sup>1),2)</sup>	$E_{AR}$	$I_D=6.2\text{ A}, V_{DD}=50\text{ V}$	0.5	
Avalanche current, repetitive $t_{AR}$ <sup>1)</sup>	$I_{AR}$		6.2	A
Drain source voltage slope	$dv/dt$	$I_D=6.2\text{ A}, V_{DS}=480\text{ V}, T_j=125\text{ °C}$	50	V/ns
Gate source voltage	$V_{GS}$	static	$\pm 20$	V
	$V_{GS}$	AC ( $f > 1\text{ Hz}$ )	$\pm 30$	
Power dissipation	$P_{tot}$	$T_C=25\text{ °C}$	74	W
Operating and storage temperature	$T_j, T_{stg}$		-55 ... 150	$^{\circ}\text{C}$

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
<b>Thermal characteristics</b>						
Thermal resistance, junction - case	$R_{thJC}$		-	-	1.7	K/W
Thermal resistance, junction - ambient	$R_{thJA}$	leaded	-	-	62	
	$R_{thJA}$	SMD version, device on PCB, minimal footprint	-	-	62	
		SMD version, device on PCB, 6 cm <sup>2</sup> cooling area <sup>3)</sup>	-	35	-	
Soldering temperature <sup>4)</sup>	$T_{sold}$	1.6 mm (0.063 in.) from case for 10 s	-	-	260	°C

**Electrical characteristics**, at  $T_j=25\text{ °C}$ , unless otherwise specified

**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}$ , $I_D=250\text{ }\mu\text{A}$	600	-	-	V
Avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0\text{ V}$ , $I_D=6.2\text{ A}$	-	700	-	
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_D=0.26\text{ mA}$	2.1	3	3.9	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=600\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ °C}$	-	0.1	1	$\mu\text{A}$
		$V_{DS}=600\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=150\text{ °C}$	-	-	100	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}$ , $I_D=3.9\text{ A}$ , $T_j=25\text{ °C}$	-	0.68	0.75	$\Omega$
		$V_{GS}=10\text{ V}$ , $I_D=3.9\text{ A}$ , $T_j=150\text{ °C}$	-	1.82	-	
Gate resistance	$R_G$	$f=1\text{ MHz}$ , open drain	-	1	-	
Transconductance	$g_{fs}$	$ V_{DS} >2 I_D R_{DS(on)max}$ , $I_D=3.9\text{ A}$	-	5.6	-	S

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$ $f=1\text{ MHz}$	-	620	-	pF
Output capacitance	$C_{oss}$		-	200	-	
Reverse transfer capacitance	$C_{rss}$		-	17	-	
Effective output capacitance, energy related <sup>5)</sup>	$C_{o(er)}$	$V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$ to 480 V	-	28	-	
Effective output capacitance, time related <sup>6)</sup>	$C_{o(tr)}$		-	47	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=480\text{ V},$ $V_{GS}=10\text{ V}, I_D=6.2\text{ A},$ $R_G=12\ \Omega$	-	7	-	ns
Rise time	$t_r$		-	12	-	
Turn-off delay time	$t_{d(off)}$		-	52	-	
Fall time	$t_f$		-	10	-	

**Gate Charge Characteristics**

Gate to source charge	$Q_{gs}$	$V_{DD}=480\text{ V}, I_D=6.2\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	3.3	-	nC
Gate to drain charge	$Q_{gd}$		-	12	-	
Gate charge total	$Q_g$		-	24	31	
Gate plateau voltage	$V_{plateau}$		-	5.5	-	V

<sup>1)</sup> Pulse width limited by maximum temperature  $T_{j,max}$  only

<sup>2)</sup> Repetitive avalanche causes additional power losses that can be calculated as  $P_{AV}=E_{AR} \cdot f$ .

<sup>3)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

<sup>4)</sup> Soldering temperature for TO263: 220 °C, reflow

<sup>5)</sup>  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

<sup>6)</sup>  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

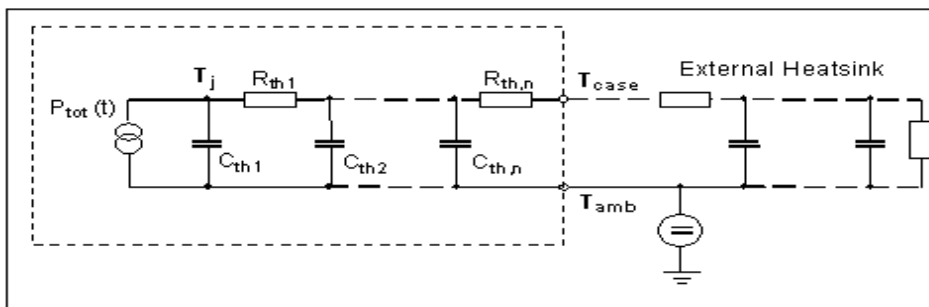
Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Reverse Diode**

Diode continuous forward current	$I_S$	$T_C=25\text{ }^\circ\text{C}$	-	-	6.2	A
Diode pulse current	$I_{S,pulse}$		-	-	18.6	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=6.2\text{ A}, T_j=25\text{ }^\circ\text{C}$	-	0.97	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=480\text{ V}, I_F=I_S, di_F/dt=100\text{ A}/\mu\text{s}$	-	400	-	ns
Reverse recovery charge	$Q_{rr}$		-	3.5	-	$\mu\text{C}$
Peak reverse recovery current	$I_{rrm}$		-	25	-	A

**Typical Transient Thermal Characteristics**

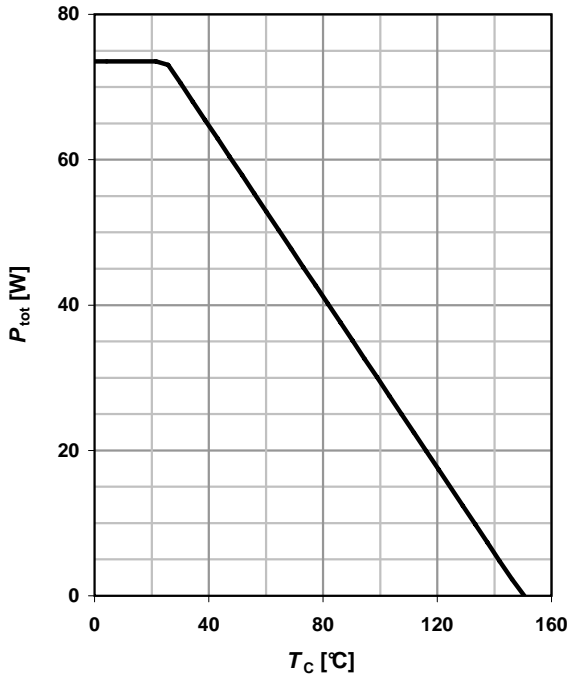
Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
$R_{th1}$	0.0325	K/W	$C_{th1}$	0.0000502	Ws/K
$R_{th2}$	0.0448		$C_{th2}$	0.000303	
$R_{th3}$	0.251		$C_{th3}$	0.000428	
$R_{th4}$	0.31		$C_{th4}$	0.00243	
$R_{th5}$	0.301		$C_{th5}$	0.00526	
			$C_{th6}$	$1.09^{7)}$	



<sup>7)</sup>  $C_{th6}$  models the additional heat capacitance of the package in case of non-ideal cooling. It is not needed if  $R_{thCA}=0\text{ K/W}$ .

**1 Power dissipation**

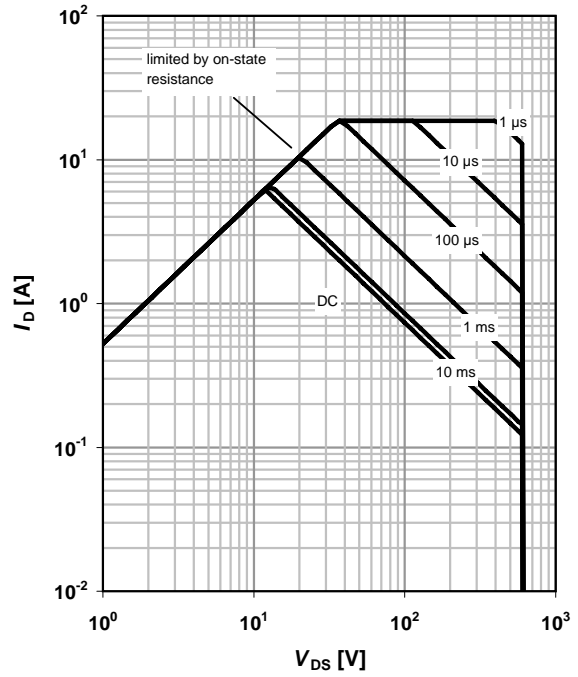
$P_{tot}=f(T_C)$



**2 Safe operating area**

$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$

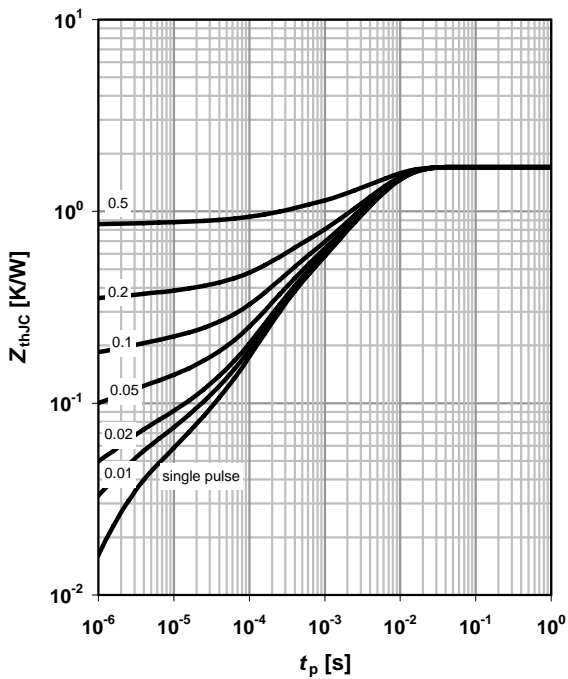
parameter:  $t_p$



**3 Max. transient thermal impedance**

$I_D=f(V_{DS}); T_j=25\text{ °C}$

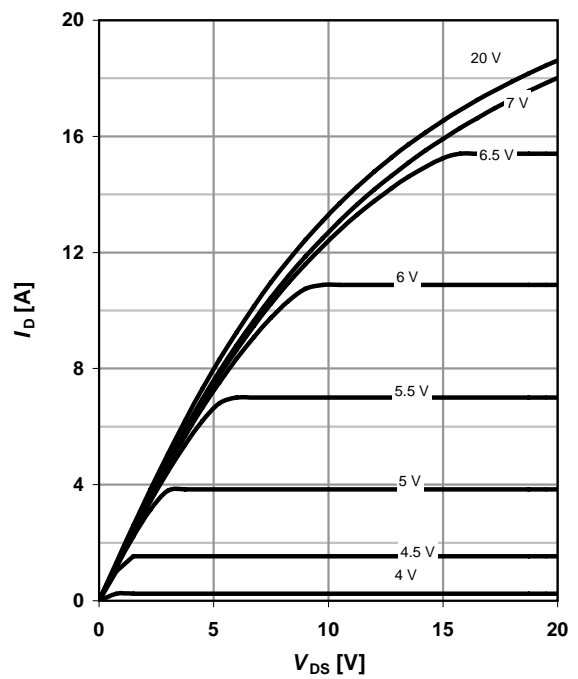
parameter:  $D=t_p/T$



**4 Typ. output characteristics**

$I_D=f(V_{DS}); T_j=25\text{ °C}$

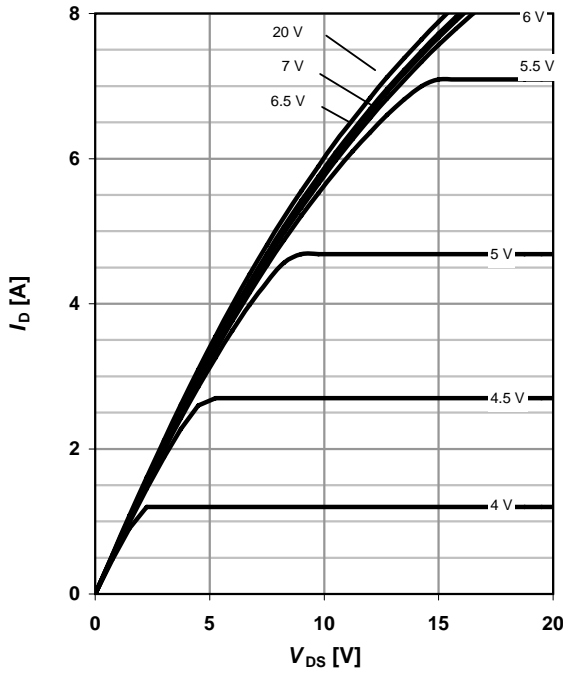
parameter:  $V_{GS}$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 150\text{ }^\circ\text{C}$

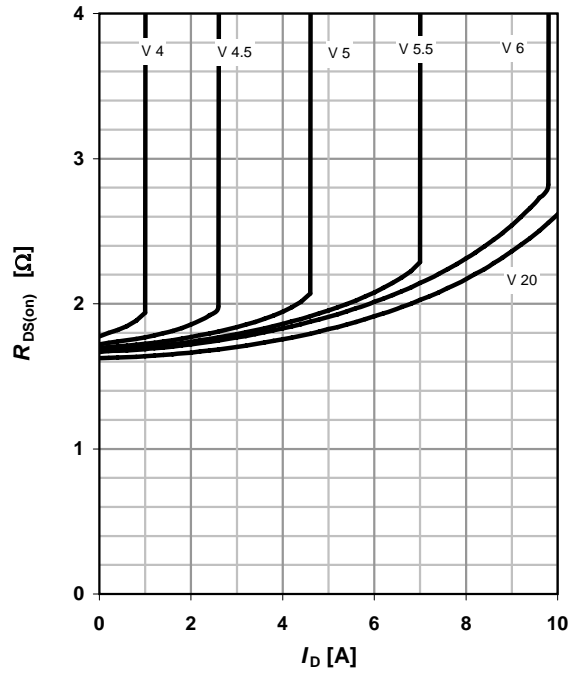
parameter:  $V_{GS}$



**6 Typ. drain-source on-state resistance**

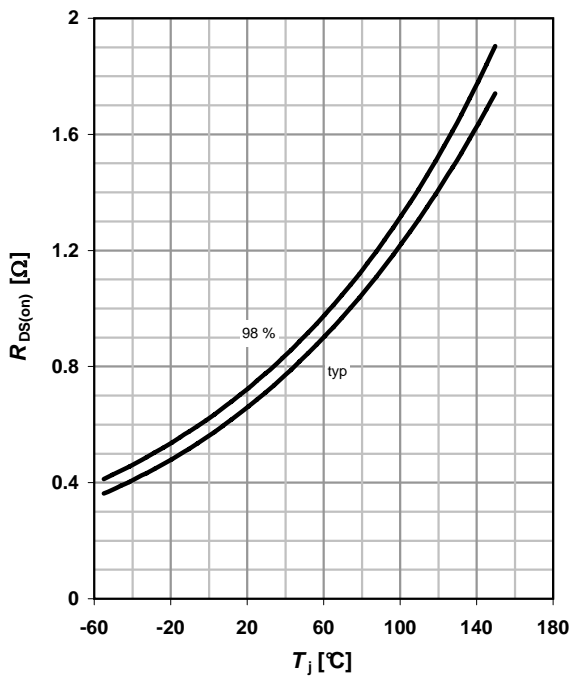
$R_{DS(on)} = f(I_D); T_j = 150\text{ }^\circ\text{C}$

parameter:  $V_{GS}$



**7 Drain-source on-state resistance**

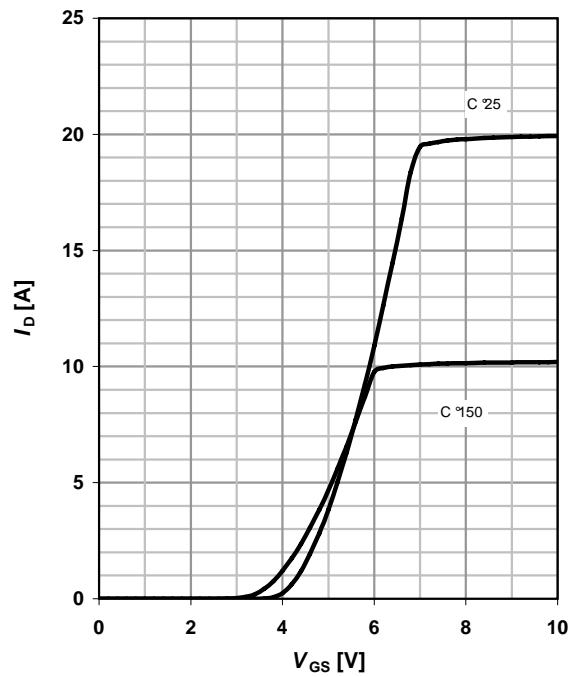
$R_{DS(on)} = f(T_j); I_D = 3.9\text{ A}; V_{GS} = 10\text{ V}$



**8 Typ. transfer characteristics**

$I_D = f(V_{GS}); |V_{DS}| > 2 I_D R_{DS(on)max}$

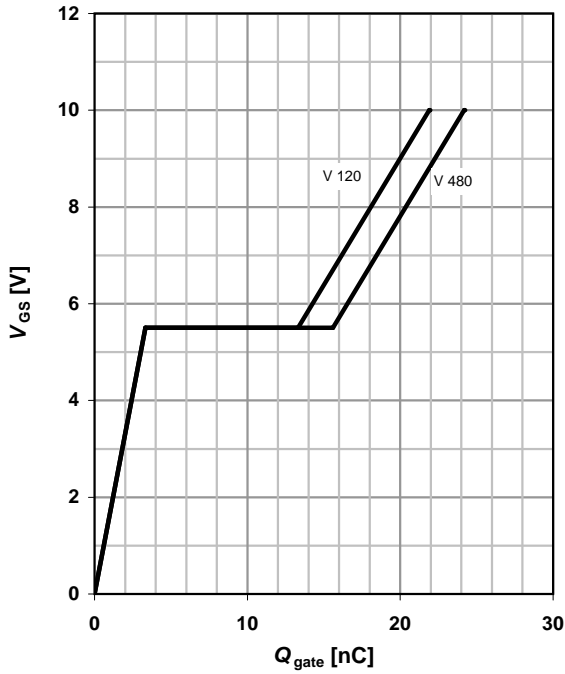
parameter:  $T_j$



**9 Typ. gate charge**

$V_{GS}=f(Q_{gate}); I_D=6.2\text{ A pulsed}$

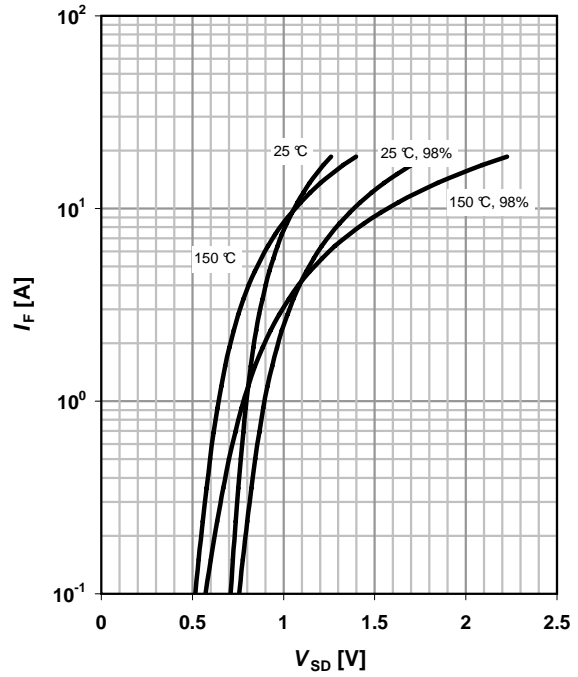
parameter:  $V_{DD}$



**10 Forward characteristics of reverse diode**

$I_F=f(V_{SD})$

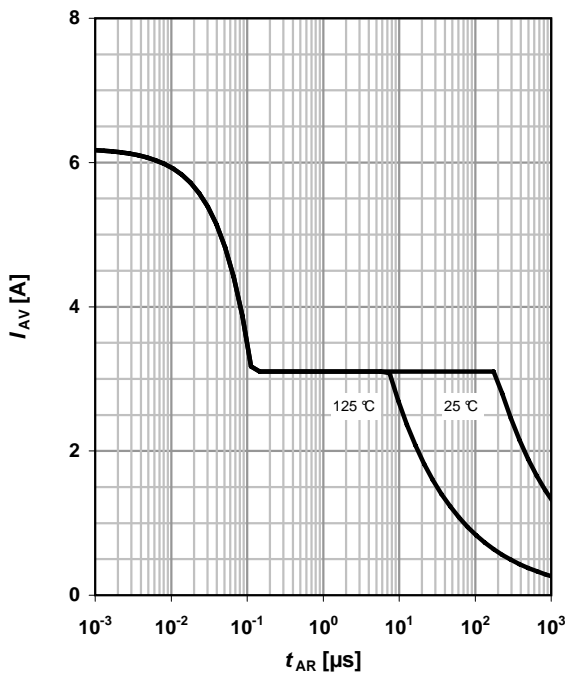
parameter:  $T_j$



**11 Avalanche SOA**

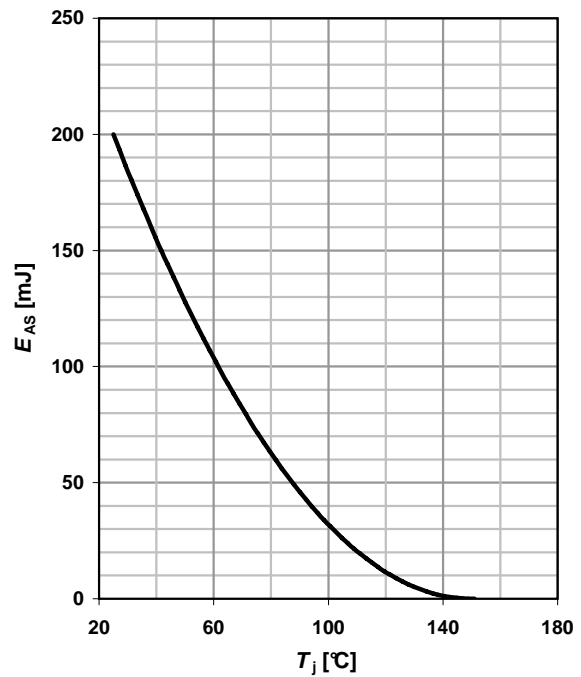
$I_{AR}=f(t_{AR})$

parameter:  $T_{j(start)}$



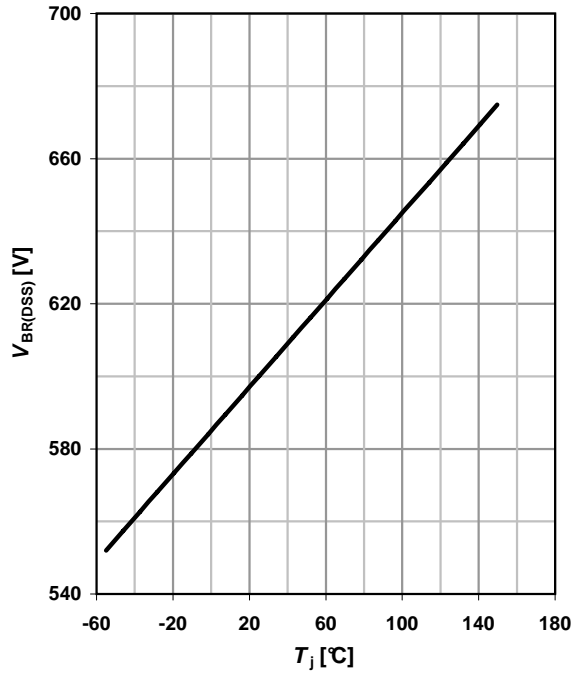
**12 Avalanche energy**

$E_{AS}=f(T_j); I_D=3.1\text{ A}; V_{DD}=50\text{ V}$



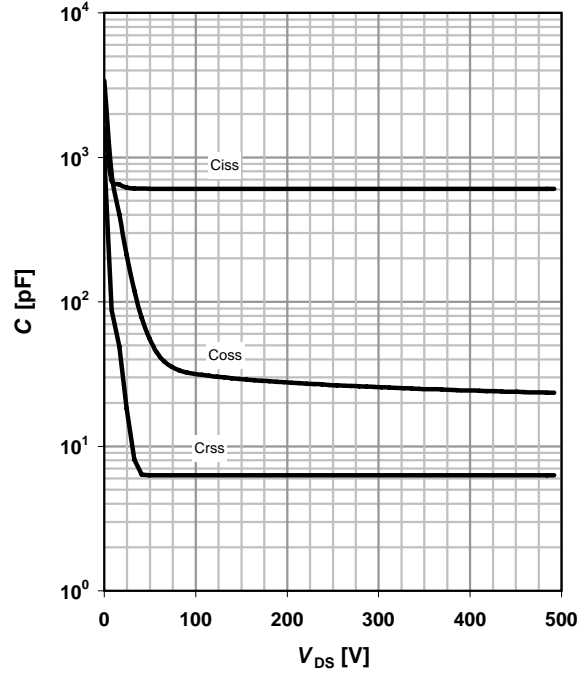
**13 Drain-source breakdown voltage**

$V_{BR(DSS)} = f(T_j); I_D = 0.25 \text{ mA}$



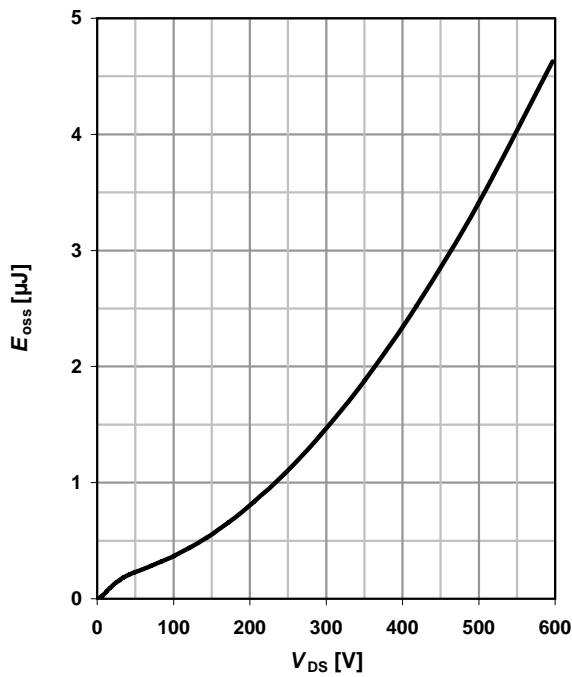
**14 Typ. capacitances**

$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



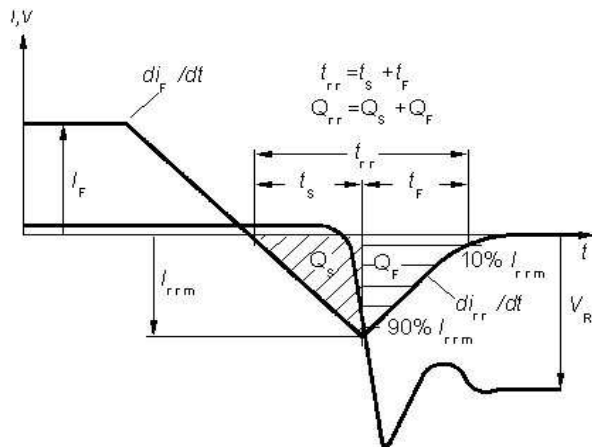
**15 Typ. C<sub>oss</sub> stored energy**

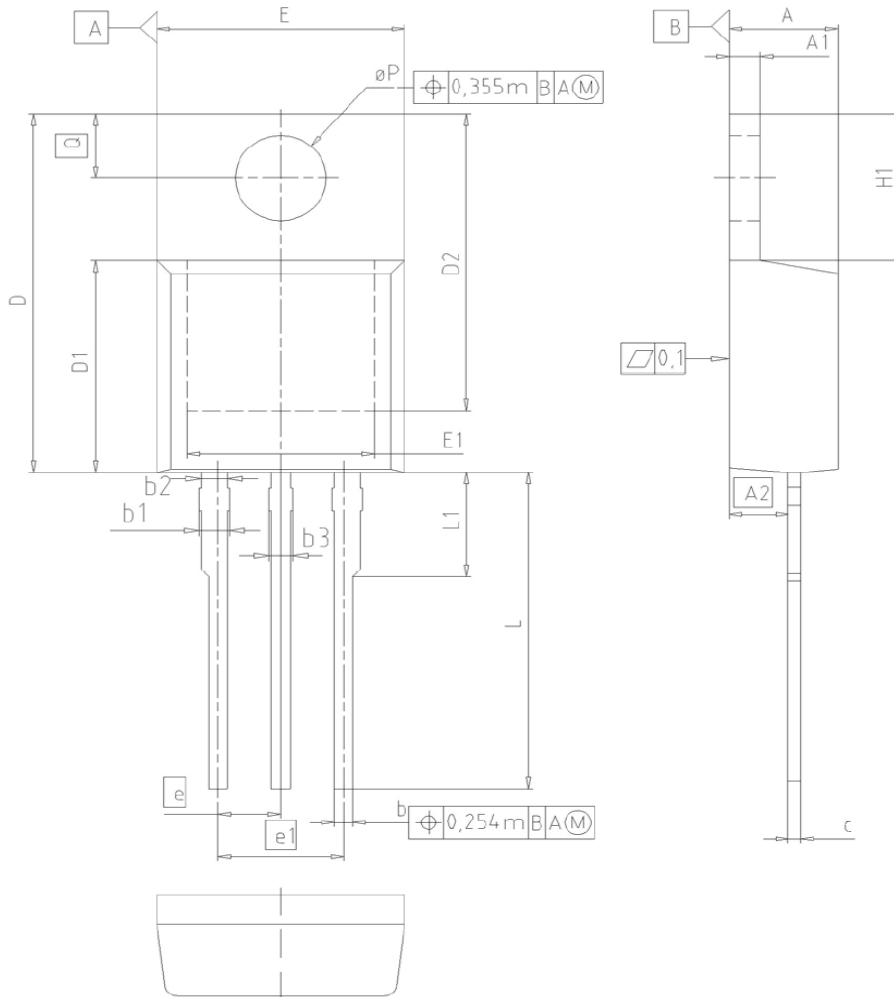
$E_{oss} = f(V_{DS})$





Definition of diode switching characteristics





DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
$\phi P$	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

**DOCUMENT NO.**  
Z8B00003318

**SCALE**  
0 2.5 5mm

**EUROPEAN PROJECTION**

**ISSUE DATE**  
23-08-2007

**REVISION**  
05

**Published by**  
**Infineon Technologies AG**  
**81726 Munich, Germany**  
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